TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM2LZ47

AC POWER CONTROL APPLICATIONS

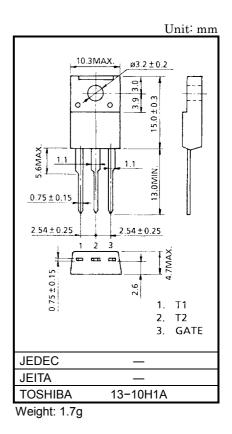
- Repetitive Peak Off-State Voltage : V_{DRM} = 800V
 - R.M.S. On–State Current : I_T (RMS) = 2A
- High Commutation (dv / dt)
- $(dv / dt) c = 5V / \mu s$ (Min.)
- : $V_{ISOL} = 1500 V AC$

MAXIMUM RATINGS

• Isolation Voltage

•

| CHARACTERISTIC | SYMBOL | RATING | UNIT | |
|---|----------------------|------------|------------------|--|
| Repetitive Peak Off-State Voltage | V _{DRM} | 800 | V | |
| R.M.S. On-State Current (Full Sine Waveform) | I _{T (RMS)} | 2 | А | |
| Peak One Cycle Surge On-State | ITSM | 8 (50Hz) | А | |
| Current (Non-Repetitive) | | 8.8 (60Hz) | A | |
| I ² t Limit Value | l ² t | 0.32 | A ² s | |
| Critical Rate of Rise of On-State Current (Note) | di / dt | 50 | Α / μs | |
| Peak Gate Power Dissipation | P _{GM} | 3 | W | |
| Average Gate Power Dissipation | P _{G (AV)} | 0.3 | W | |
| Peak Gate Voltage | V _{FGM} | 10 | V | |
| Peak Gate Current | I _{GM} | 1.6 | А | |
| Junction Temperature | Тj | -40~125 | °C | |
| Storage Temperature Range | T _{stg} | -40~125 | °C | |
| Isolation Voltage (AC, t = 1min.) | VISOL | 1500 | V | |



Note: di / dt test condition

 V_{DRM} = 400V, $I_{TM} \le 3A$, $t_{gw} \ge 10\mu$ s, $t_{gr} \le 250$ ns, i_{gp} = $I_{GT} \times 2.0$

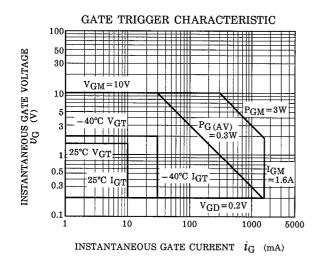
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

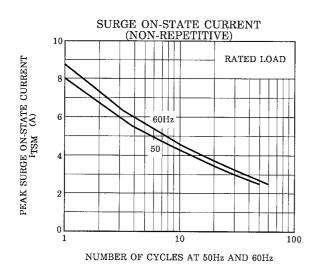
| CHARACTERISTIC | CHARACTERISTIC SYMBOL TEST CONDITION | | MIN | TYP. | MAX | UNIT | | |
|--|--------------------------------------|---|--|-------------------|-----|------|--------|--------|
| Repetitive Peak Off-State Current I _{DRM} V _{DRM} = 800V | | | _ | _ | 20 | μA | | |
| Gate Trigger Voltage | Ι | | V _D = 12V, R _L = 20Ω | T2 (+) , Gate (+) | | _ | 1.5 | v |
| | П | V _{GT} | | T2 (+) , Gate (−) | _ | _ | 1.5 | |
| | Ш | | | T2 (-) , Gate (-) | _ | _ | 1.5 | |
| Gate Trigger Current | I | | V _D = 12V, R _L = 20Ω | T2 (+) , Gate (+) | _ | _ | 10 | mA |
| | П | I _{GT} | | T2 (+) , Gate (−) | _ | _ | 10 | |
| | Ш | | - | T2 (-) , Gate (-) | _ | _ | 10 | |
| Peak On-State Voltage | | V _{TM} | I _{TM} = 3A | | _ | _ | 2.0 | V |
| Gate Non-Trigger Voltage | | V _{GD} | V _D = 800V, Tc = 125°C | | 0.2 | _ | _ | V |
| Holding Current | | Ι _Η | V _D = 12V, I _{TM} = 1A | | _ | _ | 10 | mA |
| Thermal Resistance | | R _{th (j−a)} | Junction to Ambient, AC | | | _ | 58 | °C/W |
| Critical Rate of Rise of Off-State Voltage dv / dt | | V _{DRM} = 800V, T _j = 125°C Exponential Rise | | _ | 500 | _ | V / µs | |
| Critical Rate of Rise of Off-State Vo at Communication | oltage | (dv / dt) c | V _{DRM} = 400V, T _j = 125°C (di / dt) c = - 0.5A / ms | | 5 | _ | _ | V / µs |

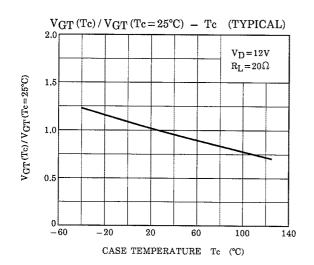
MARKING

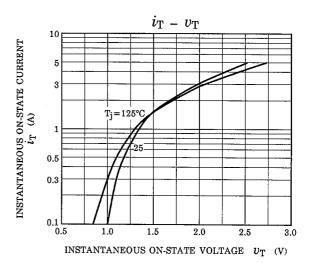
[<u>*1</u>] [<u>*2</u> [*3

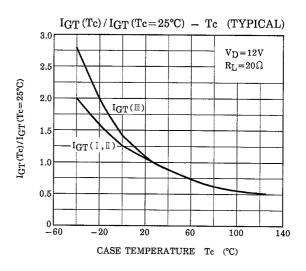
| | NUMBER | SYMBOL | | MARK | |
|---|--------|--|---------|--|--|
|] | *1 | Toshiba Product Mar | K | 5 | |
| 4 | *2 | TYPE | SM2LZ47 | M2LZ47 | |
| | *3 | Lot Number Month (Starting from) Alphabet A Year (Last Decimal Digit of the Current Year) | | Example 8A : January 1998 8B : February 1998 8L : December 1998 | |

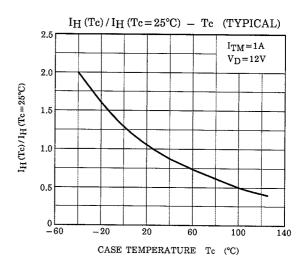




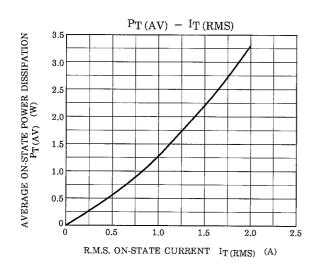


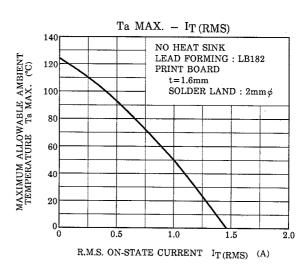




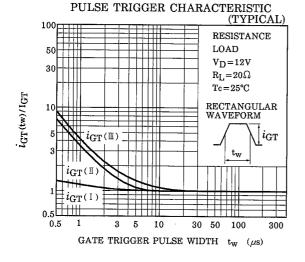


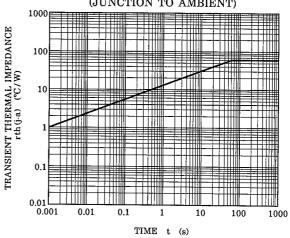
TOSHIBA





TRANSIENT THERMAL IMPEDANCE (JUNCTION TO AMBIENT)





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